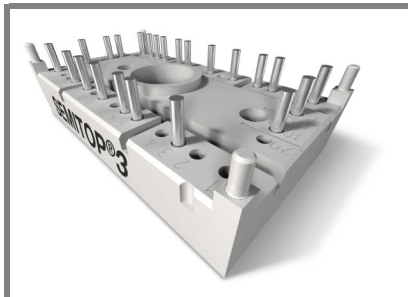


SK13GD063



SEMITOP[®] 3

IGBT Module

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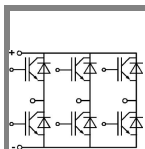
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N channel, homogeneous Silicon structure (NPT-Non punchthrough IGBT)
- High short circuit capability
- Low tail current with low temperature dependence
- UL recognized, file no. E63532

Typical Applications*

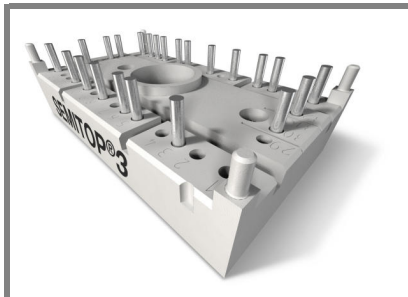
- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



GD

Absolute Maximum Ratings		T _s = 25 °C, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V _{CES}	T _j = 25 °C	600	V
I _C	T _j = 125 °C	T _s = 25 °C	18 A
		T _s = 80 °C	13 A
I _{CRM}	I _{CRM} = 2 × I _{Cnom}	20	A
V _{GES}		± 20	V
t _{psc}	V _{CC} = 300 V; V _{GE} ≤ 20 V; T _j = 125 °C V _{CES} < 600 V	10	μs
Inverse Diode			
I _F	T _j = 125 °C	T _s = 25 °C	22 A
		T _s = 80 °C	15 A
I _{FRM}	I _{FRM} = 2 × I _{Fnom}		A
I _{FSM}	t _p = 10 ms; half sine wave T _j = 150 °C	100	A
Module			
I _{t(RMS)}			A
T _{vj}		-40 ... +150	°C
T _{stg}		-40 ... +125	°C
V _{isol}	AC, 1 min.	2500	V

Characteristics		T _s = 25 °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 0,35 mA	4,5	5,5	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}	T _j = 25 °C		0,05	mA
		T _j = 125 °C			mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 30 V	T _j = 25 °C		120	nA
		T _j = 125 °C			nA
V _{CE0}		T _j = 25 °C	1		V
		T _j = 125 °C	1,1		V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C	110		mΩ
		T _j = 125 °C	90		mΩ
V _{CE(sat)}	I _{Cnom} = 10 A, V _{GE} = 15 V	T _j = 25 °C _{chiplev.}	2,1	2,5	V
		T _j = 125 °C _{chiplev.}	2	2,3	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz		0,45		nF
C _{oes}					nF
C _{res}			0,04		nF
Q _G	V _{GE} = 0 ... 20 V		54		nC
t _{d(on)}	R _{Gon} = 100 Ω	V _{CC} = 300V I _C = 10A	45		ns
t _r			45		ns
E _{on}			0,6		mJ
t _{d(off)}	R _{Goff} = 100 Ω	T _j = 125 °C V _{GE} = ±15V	250		ns
t _f			20		ns
E _{off}			0,4		mJ
R _{th(j-s)}	per IGBT			2	K/W



SEMITOR[®] 3

IGBT Module

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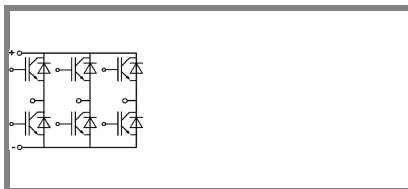
Preliminary Data

Features

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Typical Applications*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



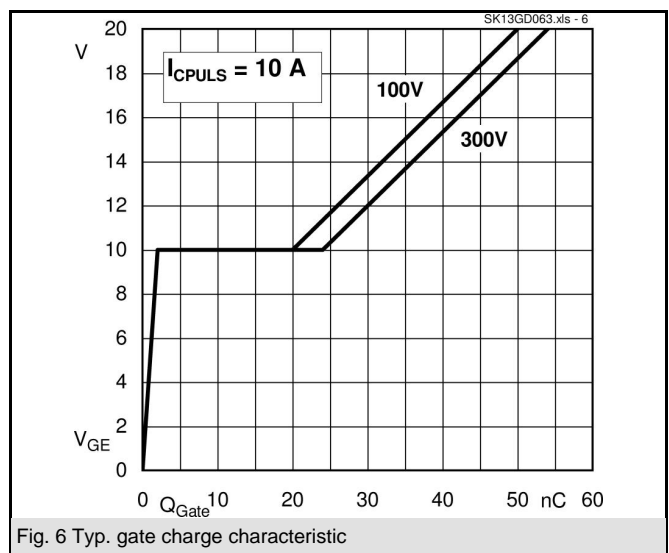
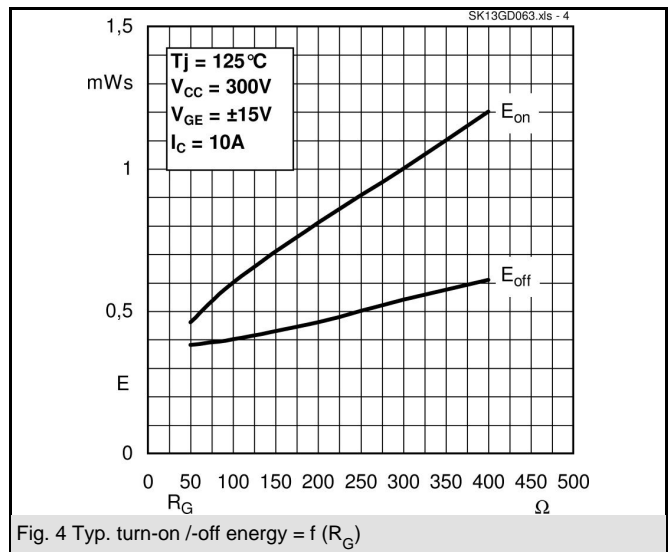
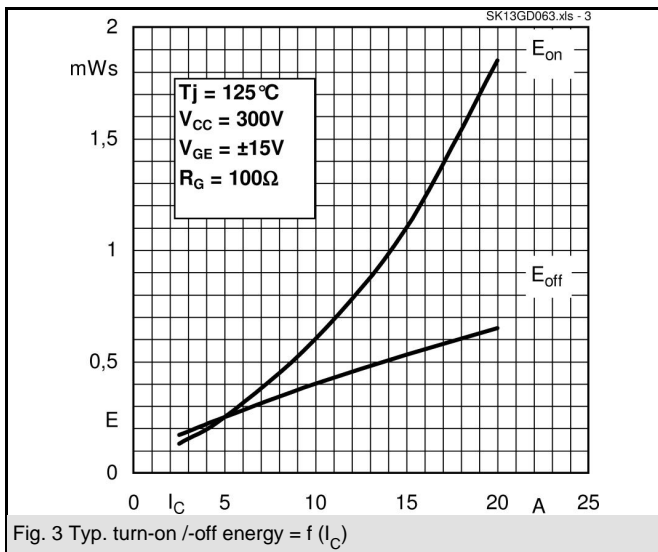
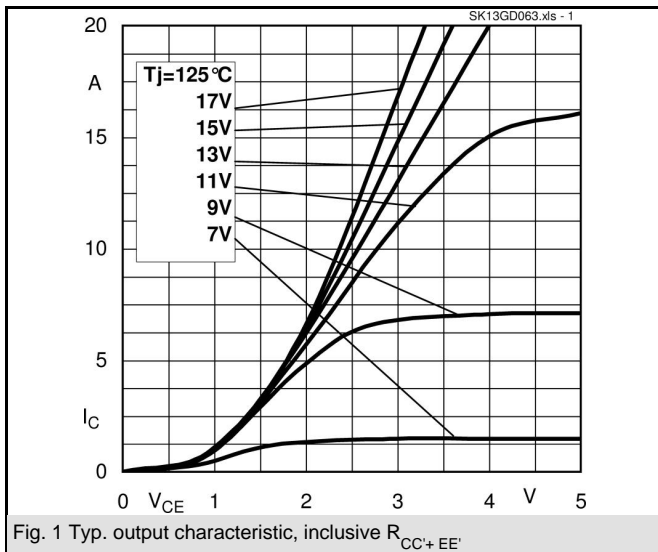
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Characteristics

Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 10 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	1,45	1,7	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,4	1,75	V
V_{F0}			0,85	0,9	V
r_F			55	80	m Ω
I_{RRM}	$I_F = 10 \text{ A}$		6,5		A
Q_{rr}	$di/dt = -200 \text{ A}/\mu\text{s}$		1		μC
E_{rr}	$V_{CC} = 300\text{V}$		0,1		mJ
$R_{th(j-s)D}$	per diode			2,3	K/W
M_s	to heat sink M1	2,25		2,5	Nm
w			30		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



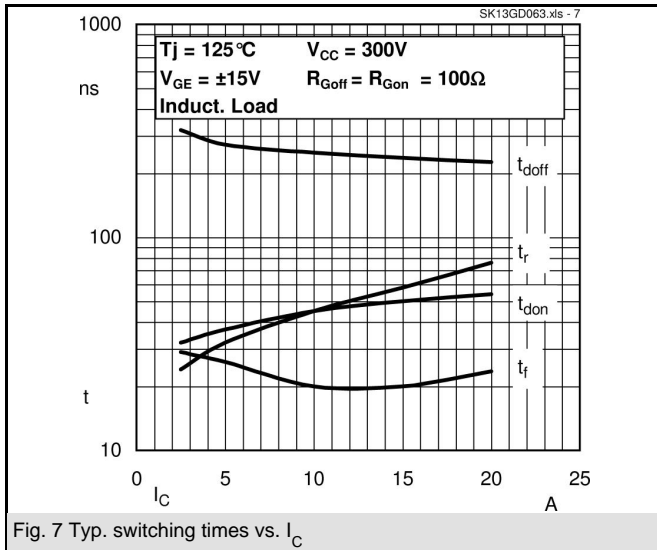


Fig. 7 Typ. switching times vs. I_C

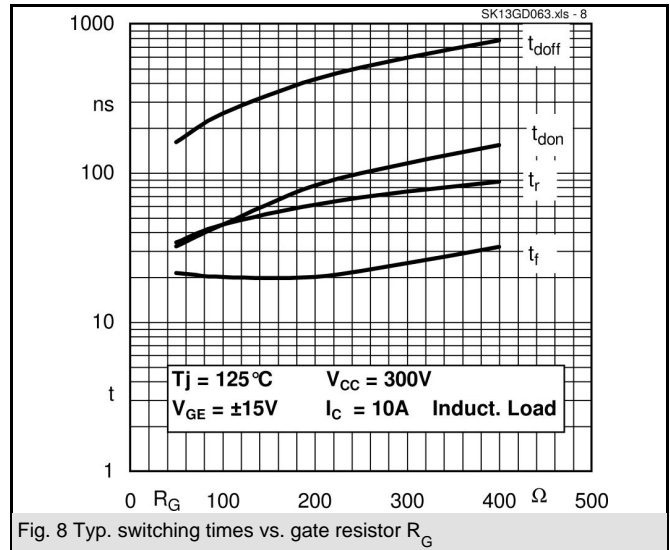


Fig. 8 Typ. switching times vs. gate resistor R_G

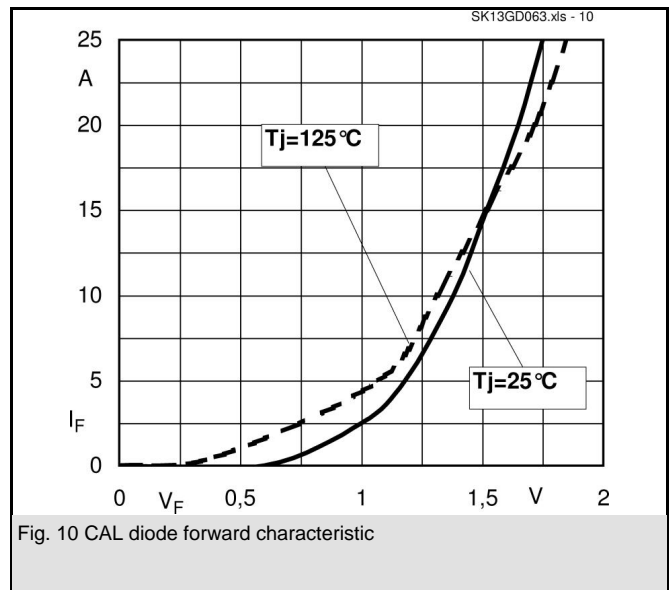
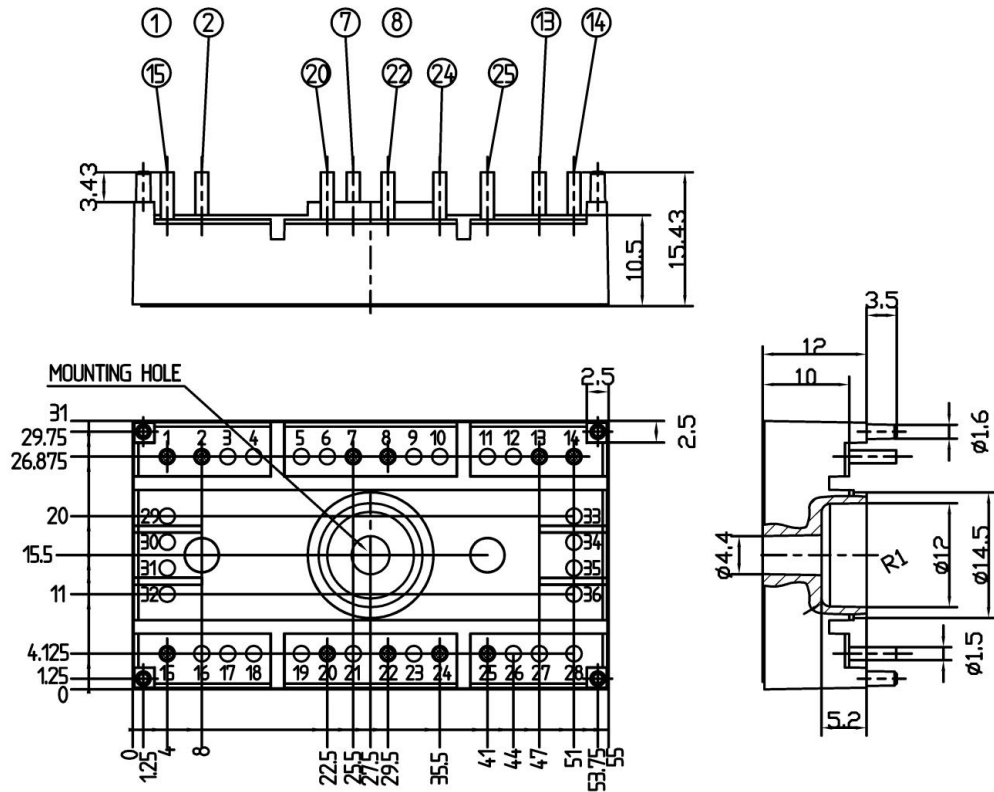


Fig. 10 CAL diode forward characteristic

SK13GD063

UL recognized file

no. E 63 532



Case T12 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)

